

Docket No.: P2001,0678

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : VOLKER HÄRLE ET AL.  
Filed : CONCURRENTLY HEREWITH  
Title : METHOD FOR FABRICATING A SEMICONDUCTOR  
COMPONENT BASED ON A NITRIDE COMPOUND  
SEMICONDUCTOR

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

U.S. Patent No. 6,130,446 (Takeuchi et al.), dated October 10, 2000;

U.S. Patent No. 6,291,839 B1 (Lester), dated September 18, 2001;

U.S. Patent No. 6,078,064 (Ming-Jiunn et al.), dated June 20, 2000;

U.S. Patent No. 6,008,539 (Shibata et al.), dated December 28, 1999;

U.S. Patent No. 5,804,839 (Hanaoka et al.), dated September 8, 1998;

European Patent Application EP 0 665 579 A1 (Chang et al.), dated August 2, 1995;

European Patent Application EP 0 542 479 A1 (Karlicek et al.), dated May 19, 1993;

European Patent Application EP 1 052 705 A1 (Ota et al.), dated November 15, 2000;

Patent Abstracts of Japan 2000091696 A (Nobuhiko et al.), dated March 31, 2000;

Patent Abstracts of Japan 2000188440 A (Hiroyuki), dated July 4, 2000;

Monemar, B. et al.: "Group III-Nitride Based Hetero and Quantum Structures",  
Elsevier Science Ltd., 2000, pp. 239-290;

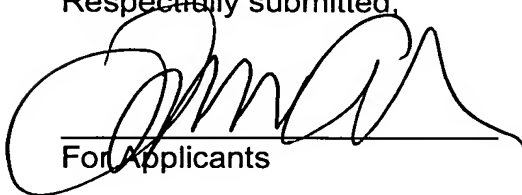
Edgar, J. H. et al.: "Properties, Processing and Applications of Gallium Nitride and  
Related Semiconductors", IEE, EMIS Daterviews Series, No. 23, Inspec 1999, pp.  
616-622;

International Search Report, dated September 23, 2003.

If no translation of pertinent portions of any foreign language patents or publications  
mentioned above is included with the aforementioned copies of those applications,  
patents and/or publications, it is because no existing translation is readily available to  
the applicant. As per the Notice in 1273 OG 55 (August 5, 2003) no copies of any  
above-mentioned U.S. patents and U.S. patent application publications are  
submitted for any application filed after June 30, 2003.

Respectfully submitted,

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For Applicants

Date: March 29, 2004

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<b>FORM PTO-1449 (SUBSTITUTE)</b>  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  <b>INFORMATION DISCLOSURE          STATEMENT BY APPLICANT</b> (37 CFR 1.98(b))				Attorney Docket No.: P2001,0678 Appl. No.:  <hr/> Applicant: VOLKER HÄRLE ET AL.  <hr/> Filing Date: March 29, 2004 Group Art Unit:			
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	6,130,446	10/10/00	Takeuchi et al.			
	B	6,291,839 B1	9/18/01	Lester			
	C	6,078,064	6/20/00	Min-Jiunn et al.			
	D	6,008,539	12/28/99	Shibata et al.			
	E	5,804,839	9/8/98	Hanaoka et al.			
	F						
	G						
	H						
	I						
<b>FOREIGN PATENT DOCUMENT</b>							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
	J	0 665 579 A1	8/2/95	Europe			
	K	0 542 479 A1	5/19/93	Europe			
	L	1 052 705 A1	11/15/00	Europe			
	M	2000091696 A	3/31/00	Japan			
	N	2000188440 A	7/4/00	Japan			
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
		Monemar, B. et al.: "Group III-Nitride Based Hetero and Quantum Structures", Elsevier Science Ltd., 2000, pp. 239-290					
		Edgar, J. H. et al.: "Properties, Processing and Applications of Gallium Nitride and Related Semiconductors", IEE, EMIS Dataviews Series, No. 23, Inspec 1999, pp. 616-622					
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			